



### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-30V	45mΩ@-10V	-4.2A
	57mΩ@-4.5V	

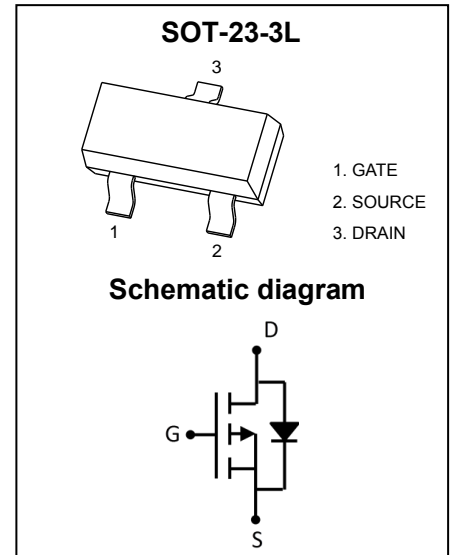
### Feature

- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance

### Application

- Load Switch
- PWM Applications

### MARKING:



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	-30	V
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1,5</sup>	$I_D$	-4.2	A
	$T_A = 25^\circ\text{C}$		
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	-16	A
Power Dissipation <sup>4,5</sup>	$P_D$	1.4	W
	$T_A = 25^\circ\text{C}$		
Thermal Resistance from Junction to Ambient <sup>5</sup>	$R_{\theta JA}$	89	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

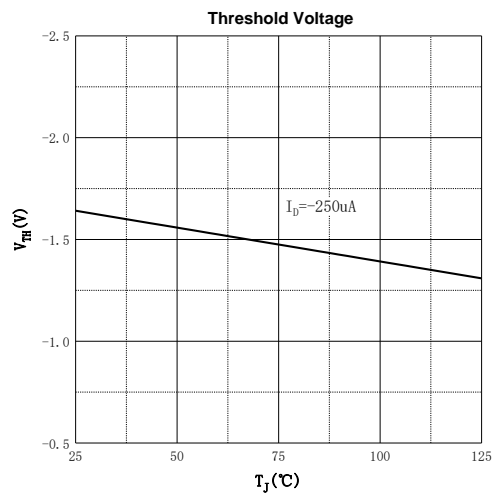
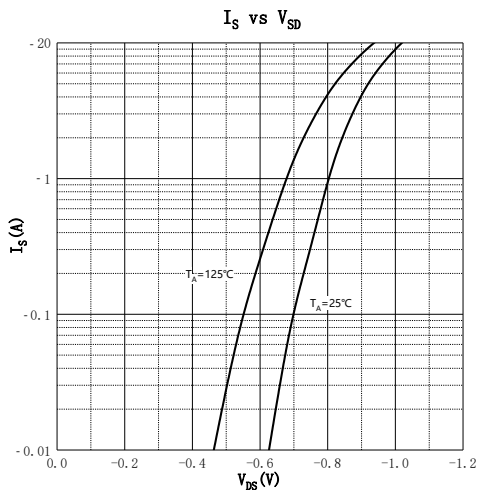
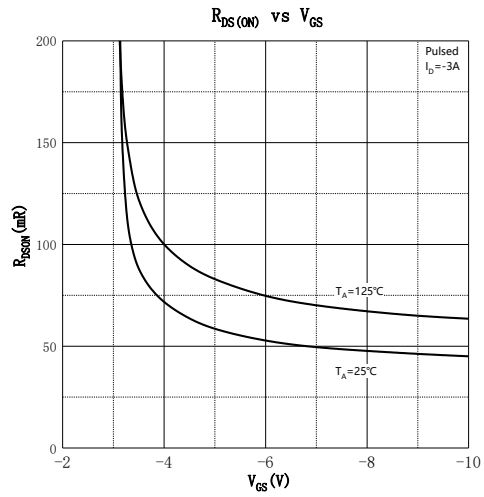
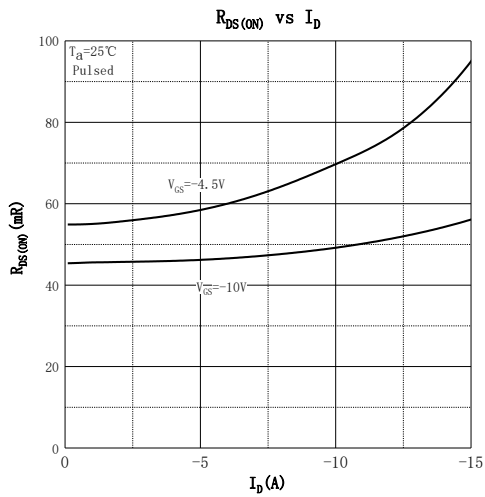
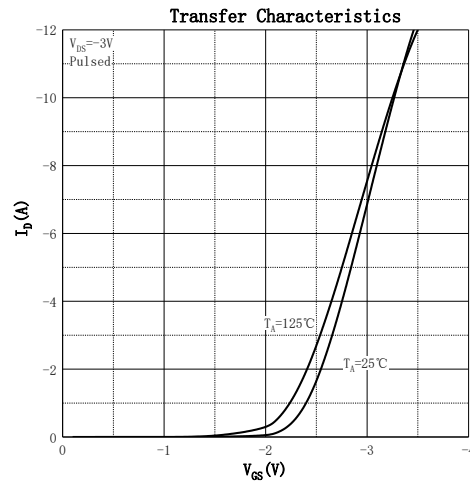
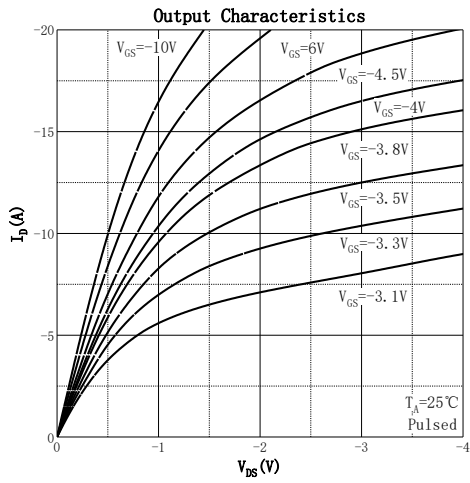
**MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)**

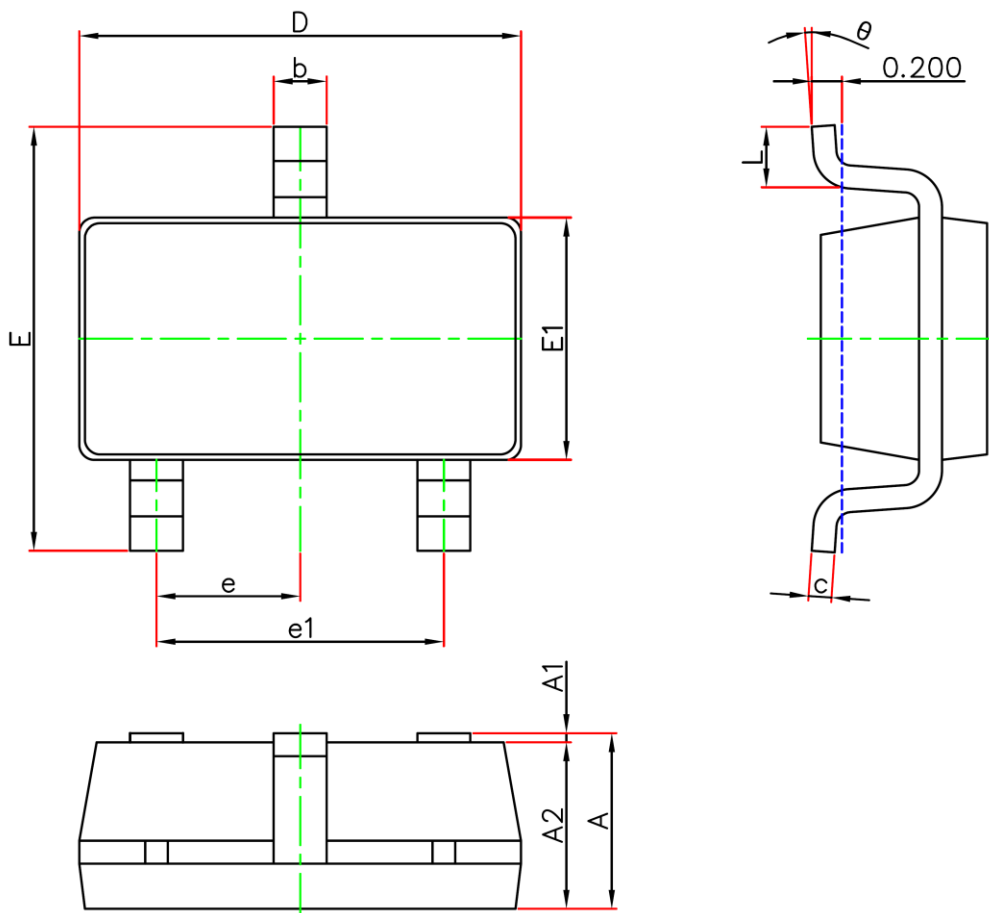
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -24V, V_{GS} = 0V$			-1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>3</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.6	-3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -4.1A$		45	60	m $\Omega$
		$V_{GS} = -4.5V, I_D = -3A$		57	87	
Forward Transconductance	$g_{FS}$	$V_{DS} = -5V, I_D = -4A$	5			S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		572		pF
Output Capacitance	$C_{oss}$			65		
Reverse Transfer Capacitance	$C_{rss}$			57		
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = -15V, V_{GS} = -10V, I_D = -4.1A$		10		nC
Gate-source Charge	$Q_{gs}$			2		
Gate-drain Charge	$Q_{gd}$			3.4		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -15V, V_{GS} = -10V,$ $R_L = 3.65\Omega, R_G = 3\Omega$		8		ns
Turn-on Rise Time	$t_r$			6.2		
Turn-off Delay Time	$t_{d(off)}$			25		
Turn-off Fall Time	$t_f$			10		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = -2A$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 4.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .
- 5.Device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

**Typical Characteristics**



**SOT-23-3L Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0	0.150	0.000	0.006
A2	1.050	1.250	0.041	0.049
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	2.650	2.950	0.104	0.116
E1	1.500	1.700	0.059	0.067
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°